

**LED 660 nm**

**1. General Description**

The Transmitter is especially appropriate for plastic fiber optic applications up to 1 mm fiber diameter. The high performance of the 660 nm LED makes this transmitter a good choice in data transmission systems with plastic fibers.

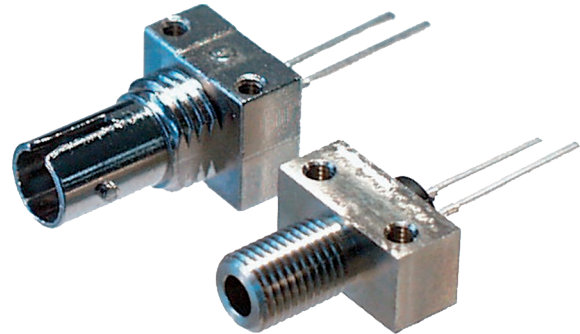
**2. Application**

Due to the good optical and mechanical features this transmitter may be used in many applications:

- Optical Networks
- Industrial Electronics
- Power Electronics
- Light Barriers

**3. Ordering Information**

<b>Model:</b>	<b>Order Number:</b>
F-SMA	905SE660SM106
F-SMA with accessories	905SE660SM1Z6
F-ST	905SE660ST106
F-ST with accessories	905SE660ST1Z6



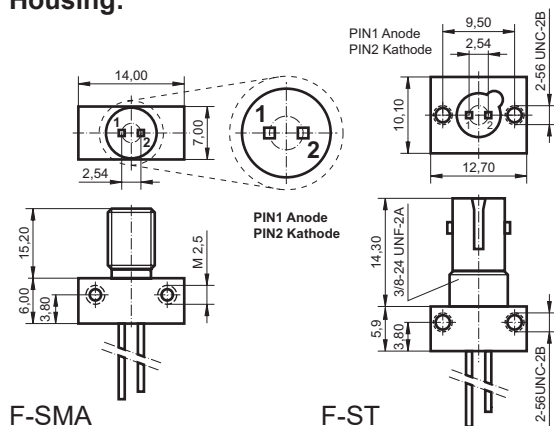
Pic 1 F-ST, F-SMA Metall Receptacle

**4. Features**

- 660 nm LED
- F-SMA metal port
- F-ST metal port
- Qualified for plastic and PCF fiber
- Metal housing
- Wave soldering compatible

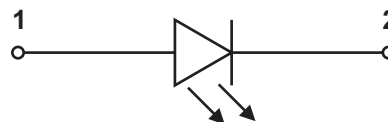
**5. Drawings**

**Housing:**



Pic 2 Drawings F-ST, F-SMA Metall Receptacle

**Circuit:**



**Accessories:** Attachment nut, lock washer, screws for PCB-mounting



## LED 660 nm

### 6 Maximum Ratings ( $T_c = 25^\circ\text{C}$ ) \_\_\_\_\_

Stresses beyond those listed under 'Maximum Ratings' may cause permanent damage to the device. Listed values are stress limits only and functional operation of the device at these conditions is not recommended. Exposure to maximum rating conditions for extended periods may affect the device reliability.

Parameter	Value	Unit
Operating temperature	-20 ... +80	$^\circ\text{C}$
Storage temperature	-30 ... +100	$^\circ\text{C}$
Junction temperature	100	$^\circ\text{C}$
Lead soldering temperature 3mm from case, $t \leq 5\text{s}$	260	$^\circ\text{C}$
Reverse voltage	5	V
Forward current	50	mA
Forward pulse current $t_w \leq 10\mu\text{s}$ , $T = \text{ms}$	500	mA
Power dissipation	120	mW

### 7 Technical Data \_\_\_\_\_

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Forward voltage	$V_F$	$I_F = 20\text{mA}$		1.8	2.2	V
Power output	$P_O$	$I_F = 20\text{mA}$		5		mW
Reverse current	$I_R$	$V_R = 5\text{V}$			100	$\mu\text{A}$
Peak wavelength	$\lambda_p$	$I_F = 20\text{mA}$		660		nm
Spectral line half width	$\Delta_\lambda$	$I_F = 20\text{mA}$		25		
Half intensity beam angle	$\theta_{1/2}$	$I_F = 20\text{mA}$		$\pm 55$		deg.
Switching times	$t_r$	$I_{FP} = 20\text{mA}$		30		ns
	$t_f$			30		
Junction capacitance	$C_J$	1MHz, $V=0\text{V}$		20		pF
Temperature coefficient	$T_{POPT}$	$I_F = 10\text{mA}$		-0.5		$\%/^\circ\text{C}$
	$T_{VF}$			-1.5		$\text{mV}/^\circ\text{C}$

The information released by Ratioplast-Optoelectronics GmbH in this data sheet is believed to be accurate and reliable. However, no responsibility is assumed by Ratioplast-Optoelectronics GmbH for its use. Ratioplast-Optoelectronics GmbH reserves the right to change circuitry and specifications at any time without notification to the customer. ■